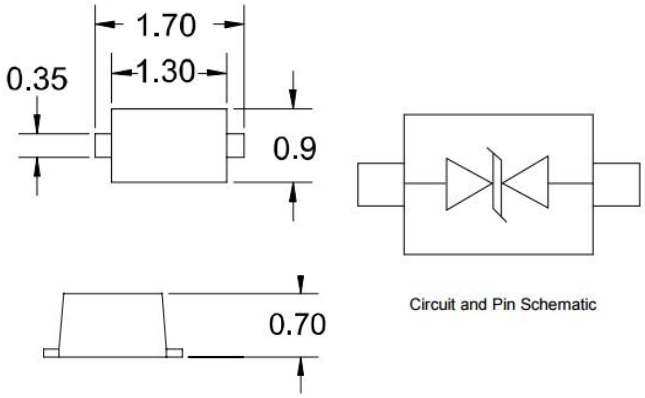
Description

The WPE0501D5 is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The WPE0501D5 has an ultra-low capacitance with a typical value at 0.3pF, and complies with the IEC 61000-4-2 (ESD) standard with ±25kV air and ±22kV contact discharge. It is assembled into a SOD- 523 leadfree package. The small size, ultra-low capacitance and high ESD surge protection make WPE0501D5 an ideal choice to protect cell phone, digital video interfaces and other high speed ports.

Features

- Ultra low capacitance: 0.3pF typical
- Ultra low leakage: nA level
- Ultra low operating voltage: 5V
- Ultra low clamping voltage
- Complies with following standards:
  – IEC 61000-4-2 (ESD) immunity test
  Air discharge: ±25kV
  Contact discharge: ±22kV
- IEC61000-4-5 (Lightning) 4A (8/20μs)
- RoHS Compliant

Dimensions & Symbol（Unit: mm Max）



Circuit and Pin Schematic

Mechanical Characteristics

- Package: SOD-523
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB 2.0 and USB 3.0 Interfaces
- PCI Express and Serial SATA Ports

Marking information

Details marking code reference customer approval list

Ordering Information

Part Number	Packaging	Reel Size
WPE0501D5	3000/Tape & Reel	7 inch

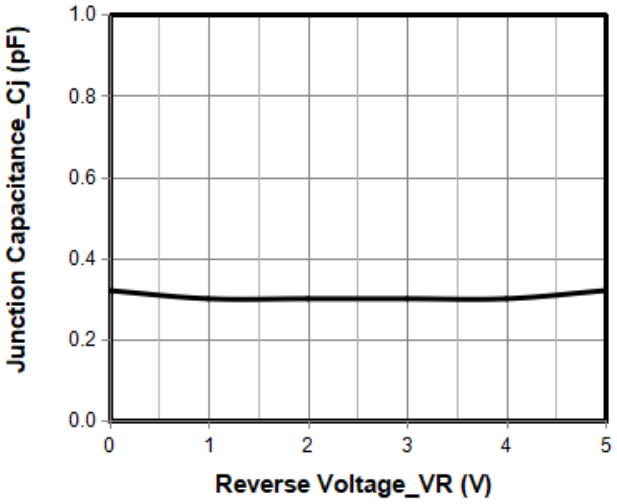
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	100	W
Peak Pulse Current (8/20μs)	Ipp	4	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	VESD	±25 ±22	kV
Operating Temperature Range	TJ	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

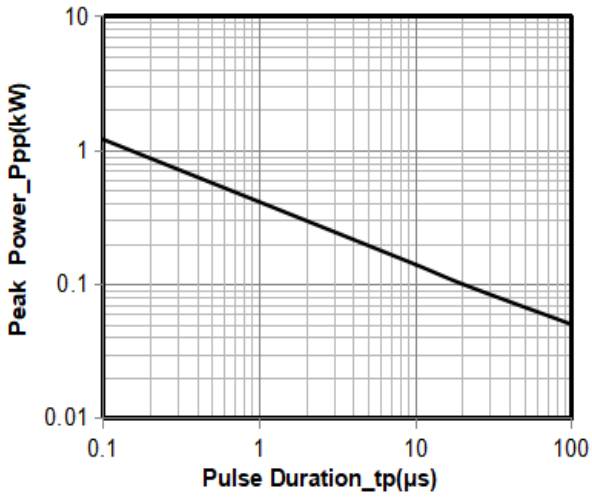
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	
Breakdown Voltage	VBR	6.5		9.5	V	IT = 1mA
Reverse Leakage Current	IR			0.2	uA	VRWM = 5V
Clamping Voltage	VC			12	V	IPP = 1A (8 x 20uS pulse)
Clamping Voltage	VC			25	V	IPP = 5A (8 x 20uS pulse)
Junction Capacitance	CJ		0.3	0.5	pF	VR = 0V, f = 1MHz

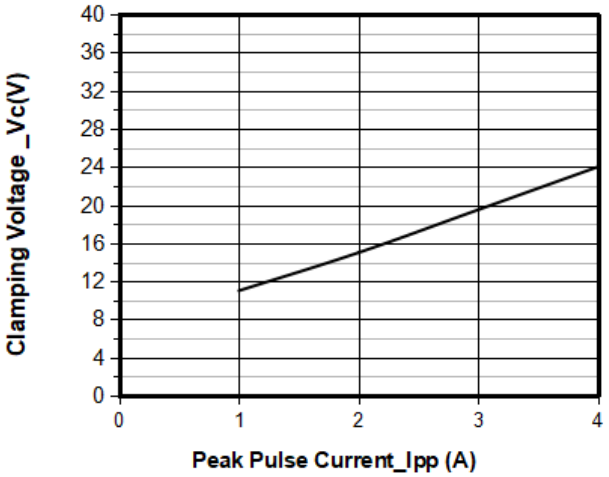
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



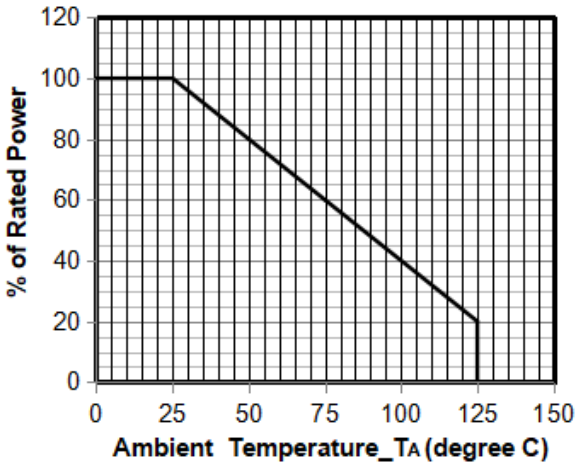
Junction Capacitance vs. Reverse Voltage



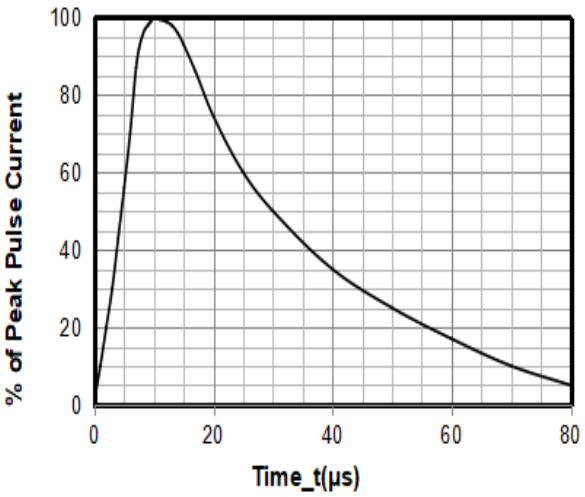
Peak Pulse Power vs. Pulse Time



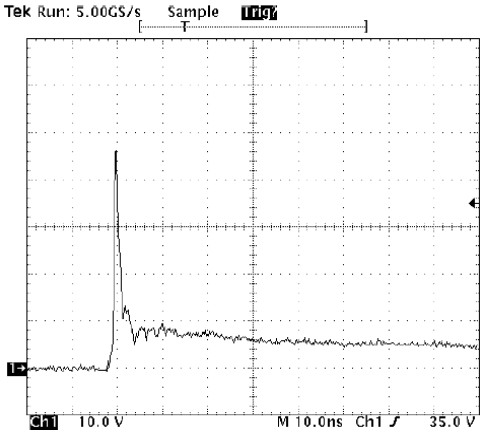
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform



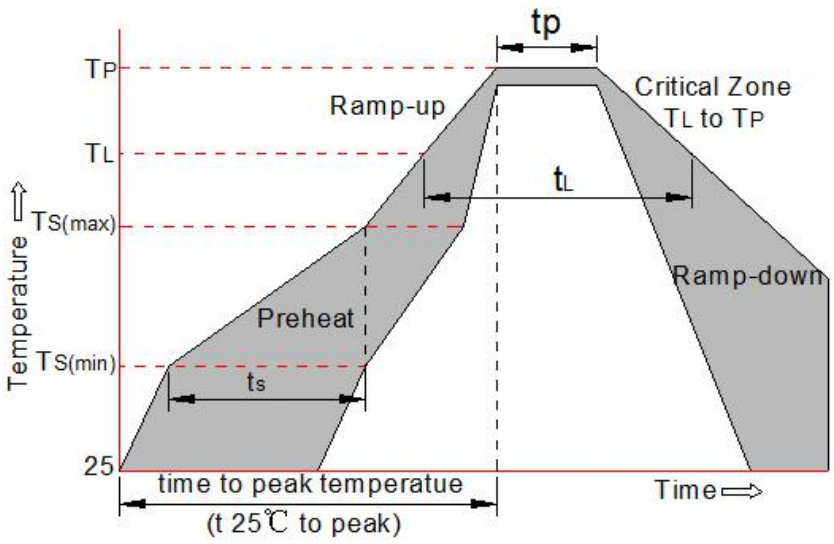
Note：Data is taken with a 10x attenuator

ESD Clamping Voltage

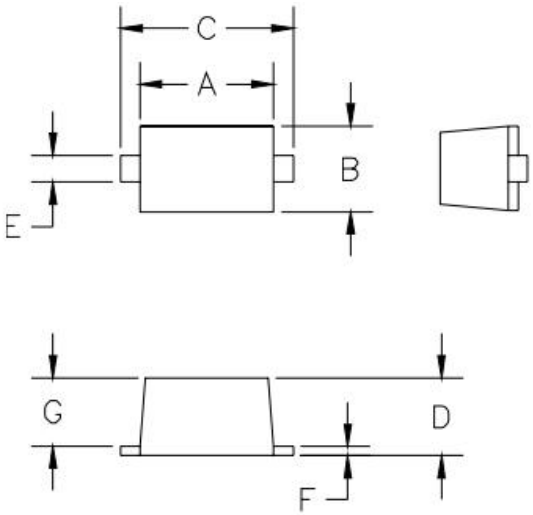
8 kV Contact per IEC61000−4−2

Soldering parameters

Reflow Condition		Pb-Free assembly (see FIG.2)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L) (Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃



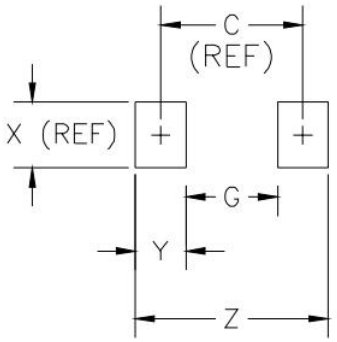
Package mechanical data



DIMENSIONS					
DIM	INCHES		MM [1]		NOTE
	MIN	MAX	MIN	MAX	
A	.043	.051	1.10	1.30	–
B	.028	.035	0.70	0.90	–
C	.059	.067	1.50	1.70	–
D	.020	.028	0.50	0.70	–
E	.010	.014	0.25	0.35	–
F	.004	.008	0.10	0.20	–
G	.020	.028	0.50	0.70	–

[1] CONTROLLING DIMENSION: MILLIMETERS

Suggested Land Pattern



DIMENSIONS					
DIM	INCHES		MM [1]		NOTE
	MIN	MAX	MIN	MAX	
C	–	.067	–	1.70	REF
G	–	.043	–	1.10	–
X	–	.031	–	0.80	REF
Y	–	.024	–	0.60	–
Z	–	.091	–	2.30	–

[1] CONTROLLING DIMENSION: MILLIMETERS

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